

30V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
30V	22mΩ @ V _{GS} = 10V	6.7A
	30mΩ @ V _{GS} = 4.5V	5.2A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

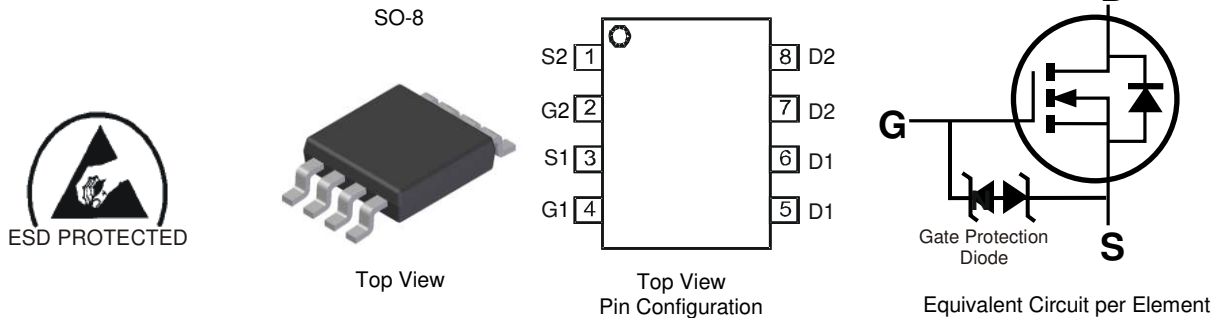
- Backlighting
- Power Management Functions
- DC-DC Converters

Features

- Low On-Resistance
- 100% UIS (Avalanche) Rated
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (Approximate)

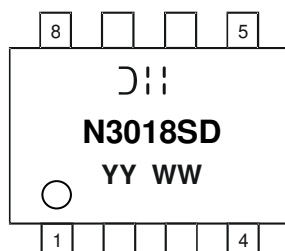


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3018SSD-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



= Manufacturer's Marking
 N3018SD = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 16 = 2016)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State T _A = +25°C T _A = +70°C	I _D	6.7
		I _D	5.3
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	t < 10s T _A = +25°C T _A = +70°C	I _D	8.7
		I _D	6.9
Maximum Body Diode Continuous Current	I _S	2.0	A
Avalanche Current (Note 6) L = 0.1mH	I _{AR}	19	A
Repetitive Avalanche Energy (Note 6) L = 0.1mH	E _{AR}	18	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State t < 10s	R _{θJA}	83
		R _{θJA}	50
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	14.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.7	2.1	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	16	22	mΩ	V _{GS} = 10V, I _D = 10A
		—	23	30		V _{GS} = 4.5V, I _D = 6A
Forward Transfer Admittance	Y _{fs}	—	8.3	—	S	V _{DS} = 5V, I _D = 6.9A
Diode Forward Voltage	V _{SD}	0.5	—	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	697	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	97	—		
Reverse Transfer Capacitance	C _{rss}	—	67	—		
Gate Resistance	R _g	—	1.47	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	6.0	—	nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 9A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	13.2	—		
Gate-Source Charge	Q _{gs}	—	2.2	—		
Gate-Drain Charge	Q _{gd}	—	1.8	—		
Turn-On Delay Time	t _{D(ON)}	—	4.3	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 15Ω, I _D = 1A, R _G = 6Ω
Turn-On Rise Time	t _R	—	4.4	—		
Turn-Off Delay Time	t _{D(OFF)}	—	20.1	—		
Turn-Off Fall Time	t _F	—	4.1	—		
Reverse Recovery Time	t _{RR}	—	7.3	—	ns	I _F = 9A, di/dt = 500A/µs
Reverse Recovery Charge	Q _{RR}	—	7.9	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

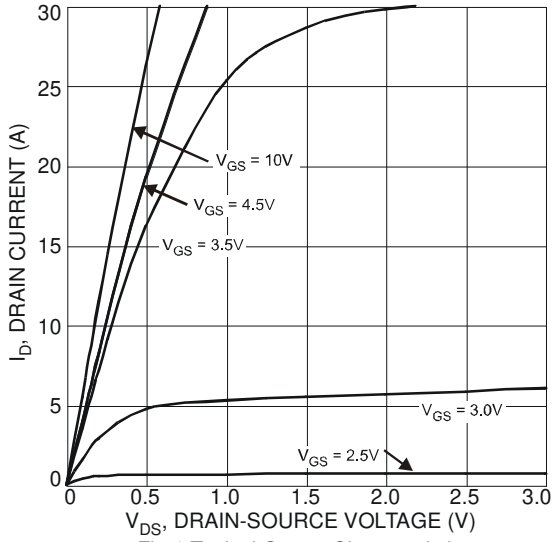


Fig. 1 Typical Output Characteristic

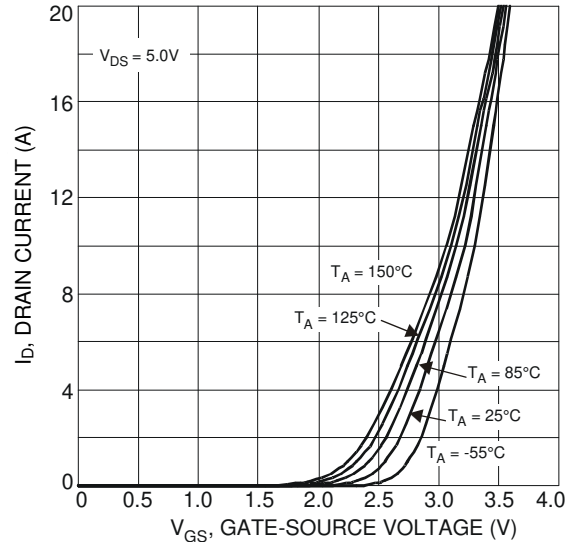


Fig. 2 Typical Transfer Characteristics

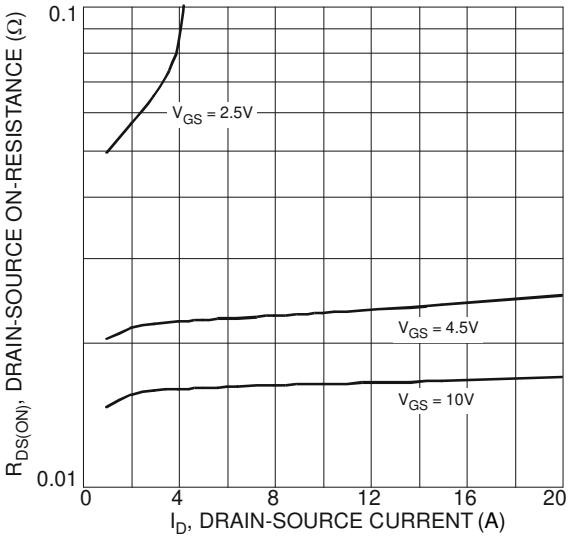


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

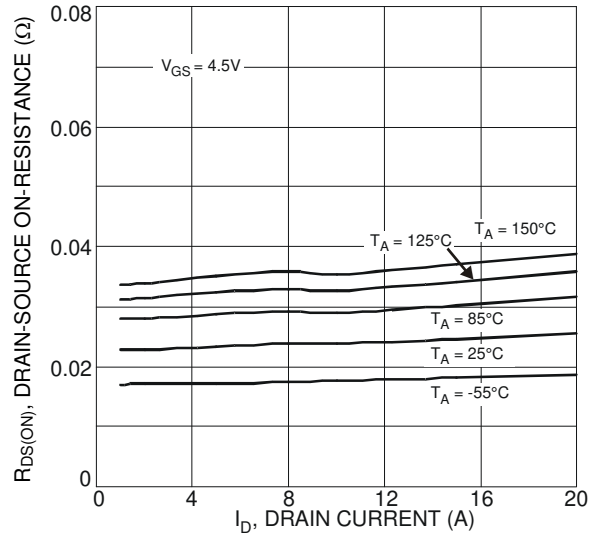


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

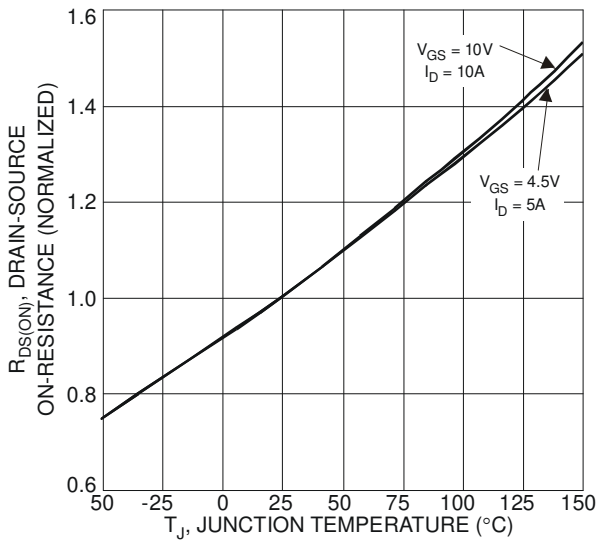


Fig. 5 On-Resistance Variation with Temperature

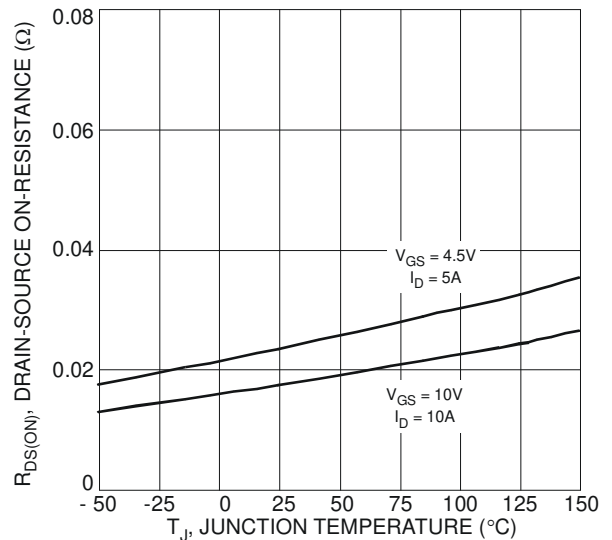


Fig. 6 On-Resistance Variation with Temperature

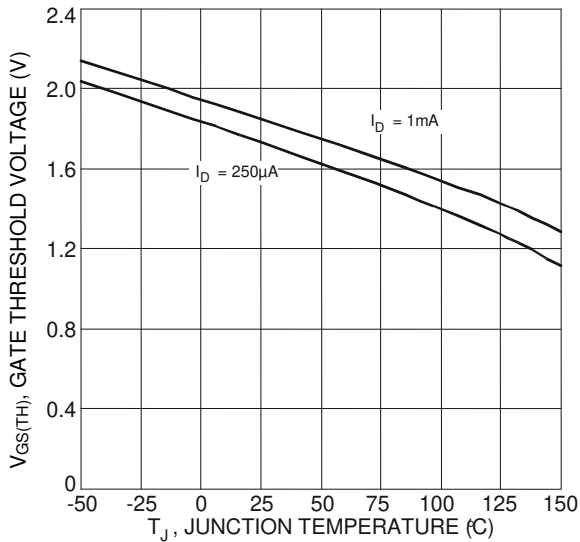


Fig. 7 Gate Threshold Variation vs. Junction Temperature

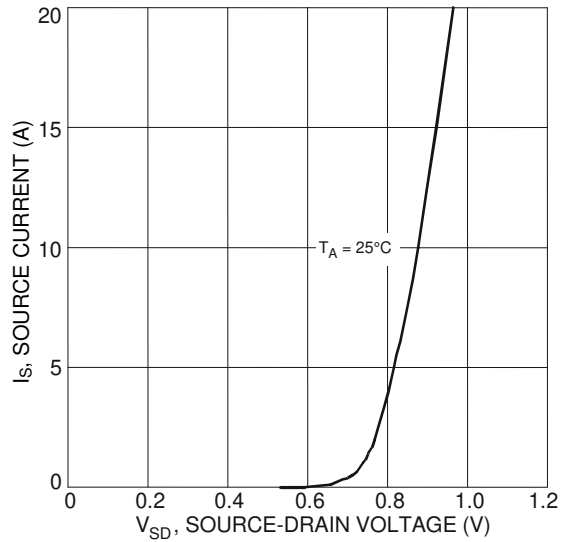


Fig. 8 Diode Forward Voltage vs. Current

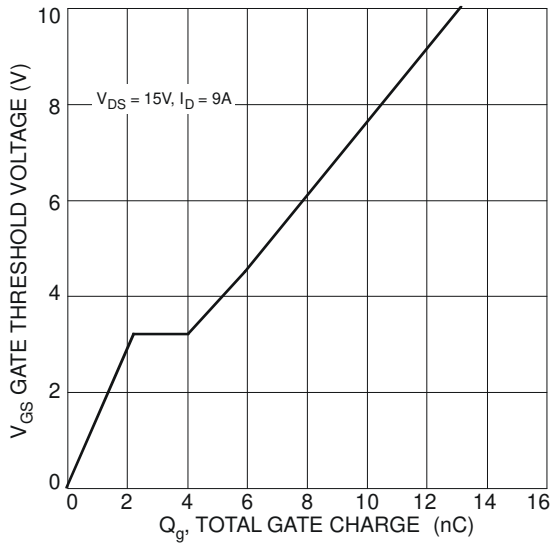


Fig. 9 Gate Charge

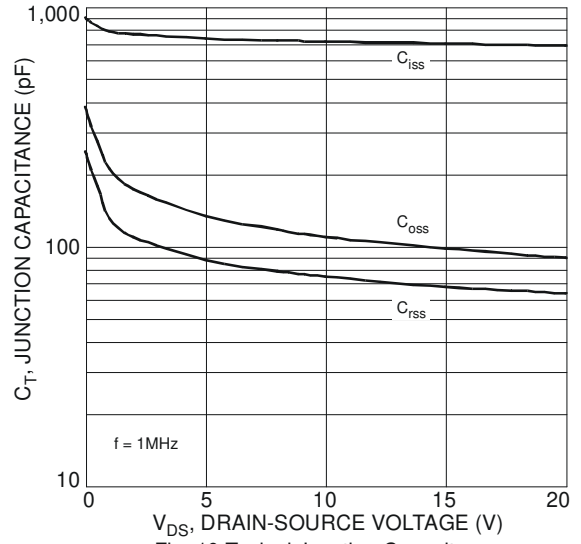


Fig. 10 Typical Junction Capacitance

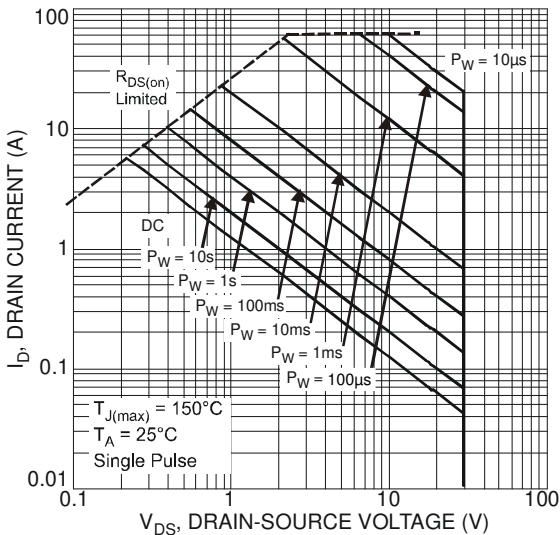


Fig. 11 SOA, Safe Operation Area

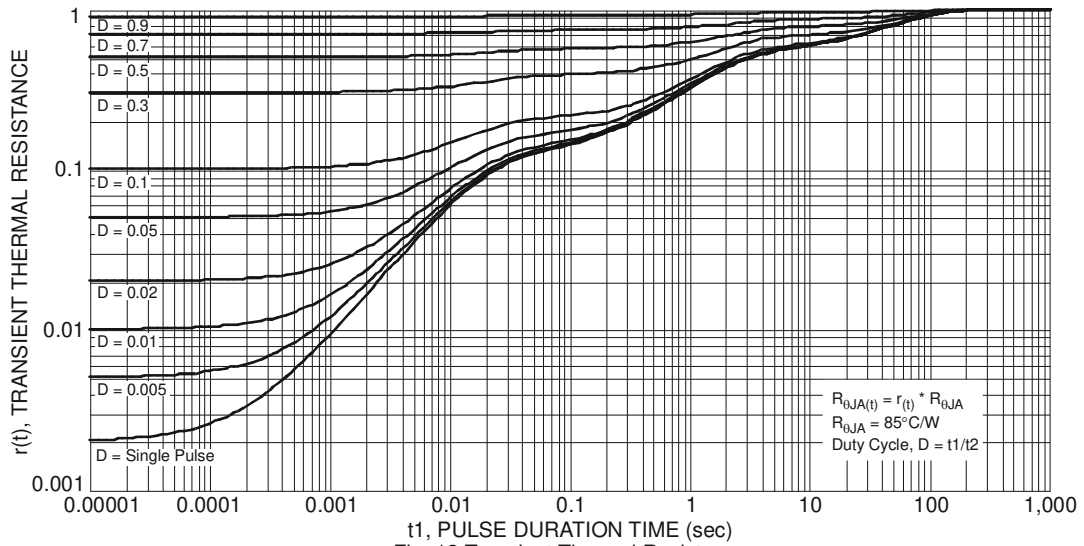
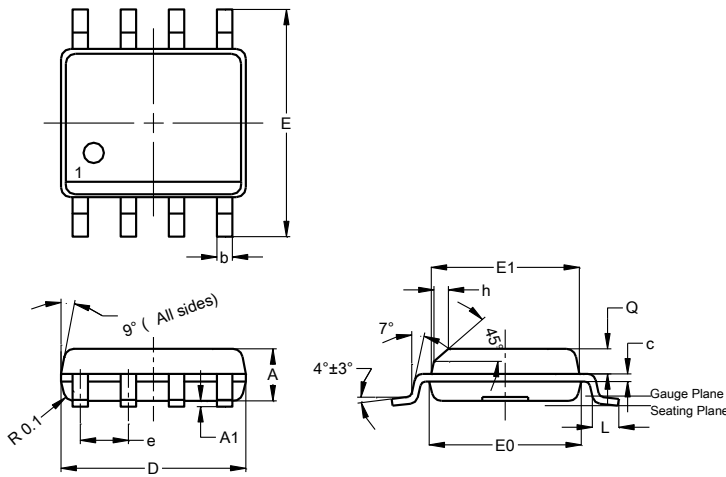


Fig. 12 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

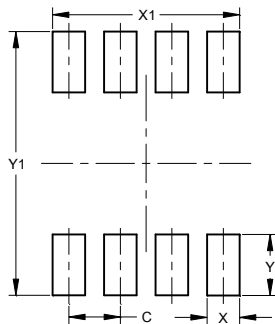


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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